N-Channel 150-V (D-S) MOSFET

Key Features:

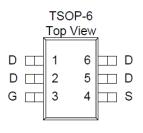
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

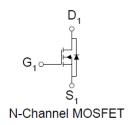
Typical	Δn	nlicatio	ns.
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$ $I_{D}(A)$			
150	700 @ V _{GS} = 10V	1.2	
130	1200 @ V _{GS} = 4.5V	1	









ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V _{DS}	150	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Brain Commental	T _A =25°	,C '	1.2		
Continuous Drain Current ^a	T _A =70°	C ID	1	Α	
Pulsed Drain Current ^b		I _{DM}	±10		
Continuous Source Current (Diode Conduction) a		Is	2.5	Α	
Dower Dissipation 8	T _A =25°		2	W	
Power Dissipation ^a	T _A =70°	C LD	1.3	VV	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W	
Maximum Junction-to-Ambient	Steady State	VθJΑ	110	C/VV	

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

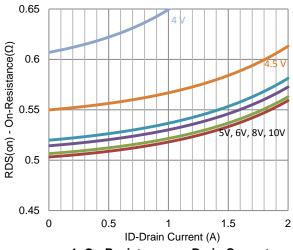
Parameter	Symbol Test Conditions		Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1		3.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA
Zero Gate Voltage Drain Current		$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	1			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 1.2 \text{ A}$			700	mΩ
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$			1200	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 1.2 \text{ A}$		5		S
Diode Forward Voltage	V_{SD}	$I_S = 1.25 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V
Dynamic						
Total Gate Charge	Q_g			2.5		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 1 \text{ A}$		1		nC
Gate-Drain Charge	Q_{gd}			0.8		
Turn-On Delay Time	t _{d(on)}			5		
Rise Time	t _r	$V_{DD} = 10 \text{ V}, R_L = 10 \Omega, I_D = 1 \text{ A},$		8		no
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = 10 V, R_{GEN} = 6 Ω		20		ns
Fall Time	t _f			10		
Input Capacitance	C _{iss}			320		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		37		pF
Reverse Transfer Capacitance	C_{rss}			20		

Notes

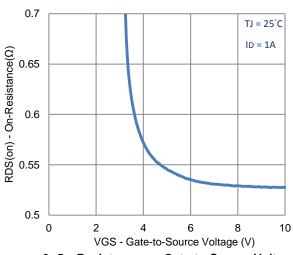
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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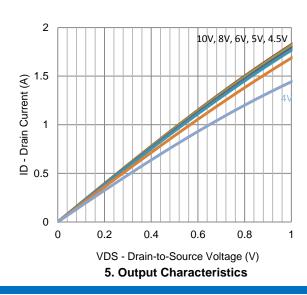
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

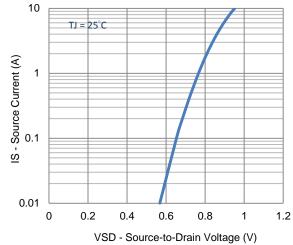


3
TJ = 25°C

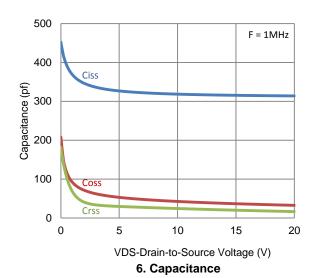
TJ = 25°C

VGS - Gate-to-Source Voltage (V)

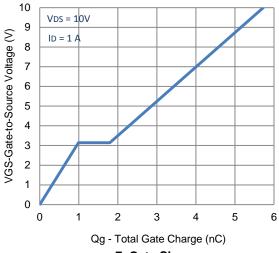
2. Transfer Characteristics

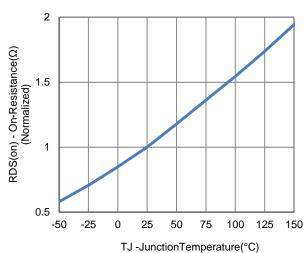


4. Drain-to-Source Forward Voltage



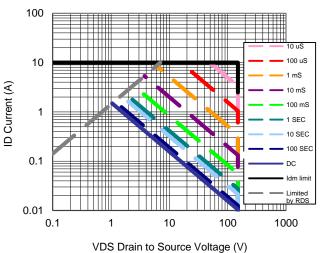
Typical Electrical Characteristics

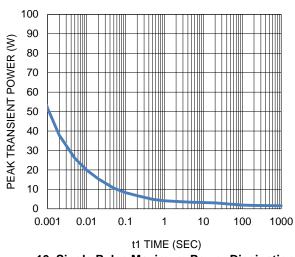




7. Gate Charge

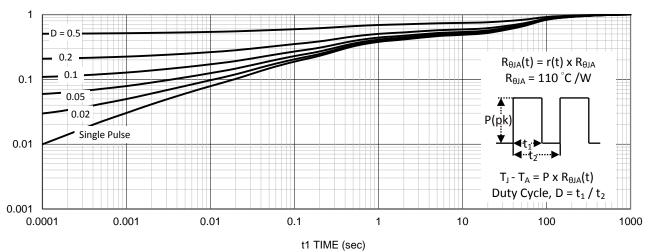
8. Normalized On-Resistance Vs Junction Temperature





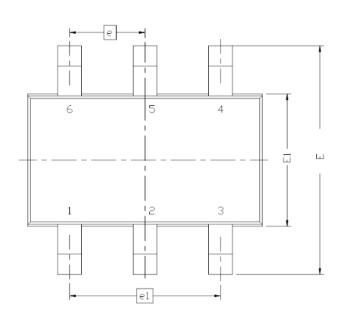
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

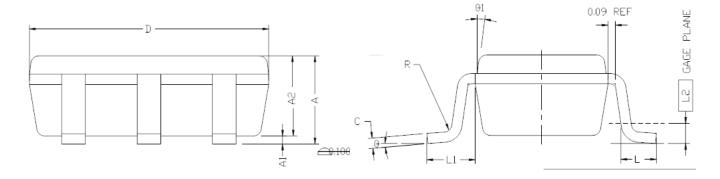


11. Normalized Thermal Transient Junction to Ambient

Package Information



DIM.	MILLIMETERS				
DIM	MIN	NDM	MAX		
Α	0.935		1.10		
A1	0.01		0.10		
A2	0.70		1.00		
b	0.25	0.32	0.40		
C	0.10	0.15	0.20		
D	2.95	2.95 3.05 3.10			
Ε	2.70 2.85 2.98		2.98		
E1			1.70		
6	0.95 BSC				
L	0.30 0.60				
L1	0.60REF				
L2	0.25BSC				
R	0.10				
θ	0?	4?	8?		
θ1	7? N□M				



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.

Ordering Information

AM3490NE-T1-XX

A: Analog Power

- M: MOSFET

- 3490: Part number

– N: N-Channel

– E: ESD Protection

- T1: Tape & reel

- XX: Blank: Standard

PF: Leadfree

Part Marking

 Line 1: Part Number/Trace Code (Example: ABYWXX)

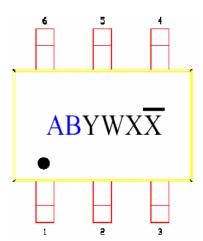
AB: Part Number code

– Y: Year Code

W: Month Code

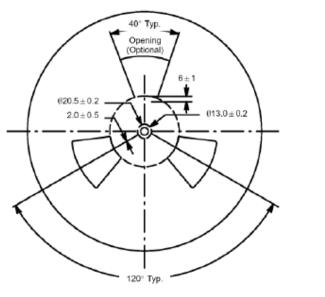
 $-X\overline{X}$: Lot Code

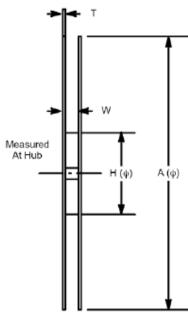
 Pb-Free Product Laser Mark: Add Bar Over Lot Code "X"



Tape & Reel Information

LOK REEL





NOTES:

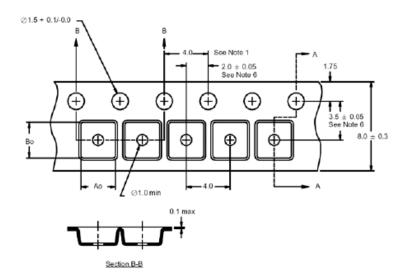
1. Material: Antistatic Plastic (High Impact Polystyrene)

Shelf Life: 2 years Color: White (Blue for special)

Application	A	W	Tape Width	Н	T
SOIC-8	330±2	12.4	12	100±2	2.5±0.5
SOT-23	172±2	0.4	9.4	55±2	2+1
TSOP-6	172±2	8.4	8.4	33±2	2±1

Tape & Reel Information

TSOP-6





NOTES:

- 1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
- 2. Camber not to exceed 1 mm in 100 mm.
- 3. Material: Conductive black Advantek polystyrene.
- 4. Ao and Bo measured on a plane 0.3 mm above the bottom of the pocket except for 3M carrier tape.
- 5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
- 6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.
- 7. All sizes in mm unless specified.
- 8. Tolerances unless specified will be \pm 0.1 mm.

Ao = 3.15 mm Bo = 3.20 mm Ko = 1.40 mm

QUANTITY PER REEL		
T1	3,000	